

**LISTING OF CLAIMS:**

1. (Currently amended) A semiconductor dynamic quantity sensor comprising:

a semiconductor substrate that has a diaphragm changing a shape thereof in accordance with an application of a dynamic quantity;

a bridge circuit that has four gauge resistors formed on the semiconductor substrate, resistances of the four gauge resistors ~~that vary~~ing based on a stress with respect to changing the shape of the diaphragm, each of the four gauge resistors ~~that has~~having a plurality of divisional gauge resistors;

a pair of first output terminals connected to a pair of respective first midpoints between the four gauge resistors, a differential electric potential between the first output terminals ~~that is~~being used as a sensor output; and

a pair of second output terminals connected to a pair of respective second midpoints between the divisional gauge resistors, a differential electric potential between the second output terminals ~~that is~~being used as a diagnostic output,

wherein at least one of the first output terminals has a plurality of terminals connected to different positions of the respective first midpoints, and

at least one of the second output terminals has a plurality of terminals connected to different positions of the respective wiring patterns formed between the divisional gauge resistors.

2. (Original) The semiconductor dynamic quantity sensor according to claim 1, wherein one of the first output terminals has not less than three terminals, and one of the second output terminals has not less than three terminals.

3. (Original) The semiconductor dynamic quantity sensor according to claim 1, wherein the second output terminals make a combination of the second midpoints at which an equal electric potential is measured when no pressure is applied to the semiconductor substrate.

4. (Currently amended) A semiconductor dynamic quantity sensor comprising:

a semiconductor substrate that has a diaphragm changing a shape thereof in accordance with an application of a dynamic quantity;

a bridge circuit that has four gauge resistors formed on the semiconductor substrate, resistances of the four gauge resistors that varying based on a stress with respect to changing the shape of the diaphragm, each of the four gauge resistors ~~that has~~ having a plurality of divisional gauge resistors;

a pair of first output terminals connected to a pair of respective first midpoints between the four gauge resistors, a differential electric potential between the first output terminals ~~that~~ is being used as a sensor output; and

a pair of second output terminals connected to a pair of respective second midpoints between the divisional gauge resistors, a differential electric potential between the second output terminals ~~that is being~~ used as a diagnostic output,

wherein at least one of the first output terminals and the second output terminals has a plurality of terminals connected to different positions of the respective first midpoints.

5. (New) The semiconductor dynamic quantity sensor according to claim 1, wherein two of the four gauge resistors are arranged close to a center of the diaphragm, and the other two of the four gauge resistors are arranged outside a peripheral edge of the diaphragm.

6. (New) The semiconductor dynamic quantity sensor according to claim 1, wherein each of the divisional gauge resistors has a same resistance.

7. (New) The semiconductor dynamic quantity sensor according to claim 4, wherein the at least one of the first output terminals and second output terminals has not less than three terminals.

8. (New) The semiconductor dynamic quantity sensor according to claim 4, wherein the second output terminals make a combination of the second midpoints at which an equal electric potential is measured when no pressure is applied to the semiconductor substrate.

9. (New) The semiconductor dynamic quantity sensor according to claim 4, wherein two of the four gauge resistors are arranged close to a center of the diaphragm, and the other two of the four gauge resistors are arranged outside a peripheral edge of the diaphragm.

10. (New) The semiconductor dynamic quantity sensor according to claim 4, wherein each of the divisional gauge resistors has a same resistance.